

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (withdrawn-previously presented) A power amplification circuit comprising:
a power amplifier; and
a serial circuit connected between a grounding terminal of the power amplifier and ground,

wherein

the serial circuit includes a diode having a variable impedance characteristic, and
wherein

the impedance of the serial circuit depends on a signal voltage occurring across the serial circuit.

2. (withdrawn- previously presented) The power amplification circuit according to Claim 1, wherein

the impedance of the serial circuit decreases as the signal voltage occurring across the circuit increases.

3. (previously presented) A power amplification circuit comprising:
a power amplifier; and
a negative feedback circuit connected between a power signal input terminal and a power signal output terminal of the power amplifier,

wherein

impedance of the negative feedback circuit depends on a signal voltage occurring across the negative feedback circuit, and

wherein

the negative feedback circuit is a series connection circuit in which a diode and a capacitance device are connected in series or a series connection circuit in which a diode, a

capacitance device and a feedback resistor are connected in series, wherein the diode has a variable impedance characteristic, and

a connecting point between the diode and the capacitance device is grounded via a grounding resistor, and

wherein

a bias power supply for the power amplifier is connected to one end of the series connection circuit so that the diode is biased.

4. (previously presented) The power amplification circuit according to Claim 3, wherein

the diode is constituted of a base-collector junction or a base-emitter junction of a bipolar transistor.

5. (original) The power amplification circuit according to Claim 4, wherein the power amplifier is constituted of a bipolar transistor, the bipolar transistor constituting the diode and the bipolar transistor used for the power amplifier are generally equal to one another in bias-current temperature characteristics.

6. (previously presented) The power amplification circuit according to Claim 3, wherein

the diode is constituted of a gate-drain junction or a gate-source junction of a field effect transistor.

7. (currently amended) A communication device comprising:
a power amplification circuit, the power amplification circuit comprising:
a power amplifier; and
a negative feedback circuit connected between a power signal input terminal and a power signal output terminal of the power amplifier,

wherein

impedance of the negative feedback circuit depends on a signal voltage occurring across the negative feedback circuit, and

wherein

the negative feedback circuit is a series connection circuit in which a diode and a capacitance device are connected in series or a series connection circuit in which a diode, a capacitance device and a feedback resistor are connected in series, wherein the diode has a variable impedance characteristic, and

wherein

the power amplification circuit is a transmitting section amplifies a transmitting signal in the communication device to a specified antenna output.

8. (new) A communication device comprising the power amplification circuit of claim 3.